## NSN 5961-01-211-0007

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Semiconductor Device Set - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-211-0007 **Inclosure Material:** Ceramic all transistor **Overall Length:** 0.975 inches all transistor **Overall Height:** 0.285 inches all transistor **Mounting Facility Quantity:** 2 all transistor **Internal Configuration:** Junction contact all transistor **Internal Junction Configuration:** Npn all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Unthreaded hole all transistor **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 70.0 breakdown voltage, collector-to-emitter, with base short-circuited to emitter and 3.0 breakdown voltage, emitter-to-base, collector open all transistor **Current Rating Per Characteristic:** 20.00 amperes collector current, dc all transistor **Power Rating Per Characteristic:** 250.0 watts total device dissipation all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction all transistor **Terminal Type And Quantity:** 4 ribbon all transistor Shelf Life: N/a **Unit Of Measure:** Demilitarization: No